

SPEC SHEET (FOR REFERENCE)	SHEET No.	G05067A	Page.
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TYPE : 6PT2302N6A**

CHIP SIZE	0.56 * 0.43 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	64,000 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	20	V
Gate-source voltage	VGSS	±12	V
Drain Current (DC)	ID	0.95	A

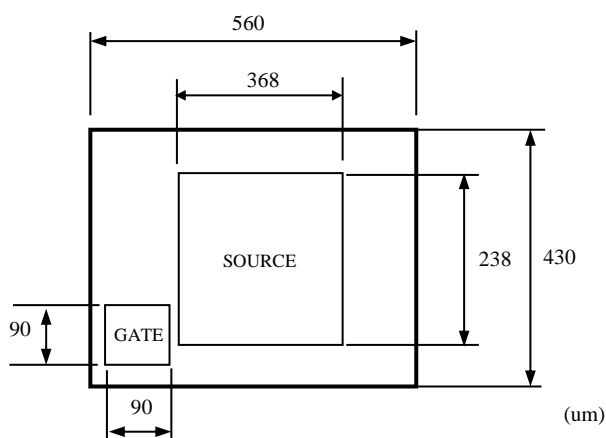
* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	VGSS	±13			V	IG=±10uA
2	IGSS 1			±10	uA	VGS=±12.0V VDS=0V
3	IGSS 2			±3	uA	VGS=±8.0V VDS=0V
4	IGSS 3			±500	nA	VGS=±4.5V VDS=0V
5	IDSS			1.0	uA	VDS=20.0V VGS=0V
6	BVDSS	23			V	ID=250uA
7	VTH	0.6		1.3	V	ID=250uA
8	Ron 1		0.13	0.25	Ω	ID=600mA VGS=4.5V
9	Ron 2		0.22	0.5	Ω	ID=500mA VGS=2.5V
10	Ron 3		0.4	1.0	Ω	ID=150mA VGS=1.8V
11	VSD	0.5		1.1	V	IS=200mA
12	YFS	200			mS	ID=500mA VDS=10V

The F/T specifications must be relaxed than the wafer probing specifications

※ Built-in ZD between Gate and Source.



TENTATIVE

NOTE: